

SSCN9018GS6

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NPN Switching Transistor

\triangleright Features

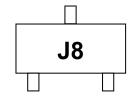
VCB	VCE	VEB	IC
30V	15V	5V	50mA

Description \succ

The NPN Transistor is designed for use in linear and switching

3 - Collector 1 - Base 0 0 -0 2 - Emitter

Circuit Diagram



Marking (Top View)

applications. The device is housed in the SOT-23 package,						
which	is	designed	for	telephony	and	professional
commur	nicat	tion equipme	ent.			

General purpose switching and amplification

Telephony and professional communication equipment

Ordering Information \geq

Applications

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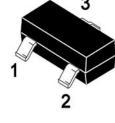
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Device	Package	Shipping
SSCN9018GS6	SOT-23	3000/Reel

3

Pin configuration

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<u>SOT-23</u>



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> Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	30	V
Collector- Emitter Voltage	V _{CEO}	15	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current-Continuous	lc	50	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	°C

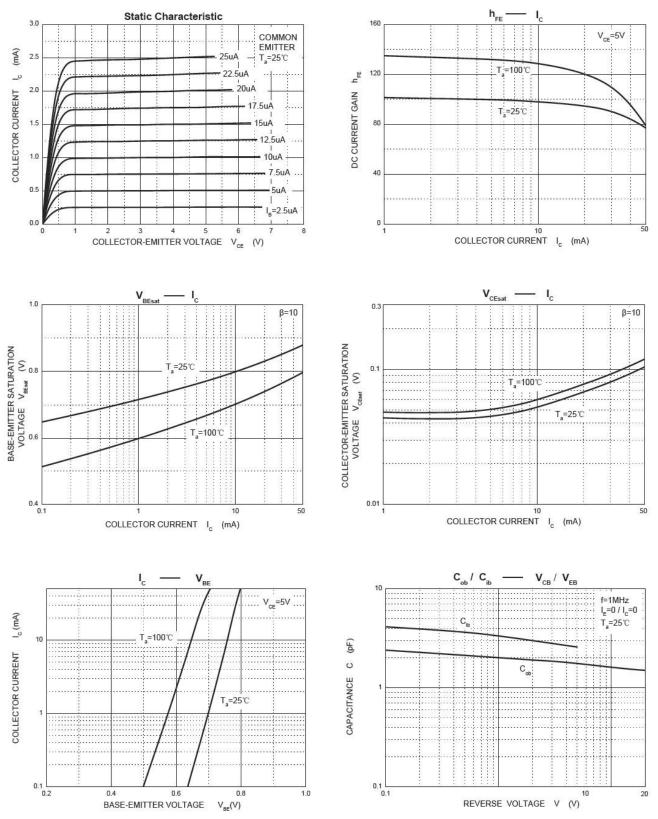
> Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100uA,I _E =0	30			V
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =1mA,I _B =0	15			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =100uA,I _C =0	6			V
Collector Cutoff Current	I _{СВО}	V _{CB} =12V, I _E =0			0.05	μA
Collector Cutoff Current	I _{CEO}	V _{CE} =12V,I _B =0			0.1	μA
Emitter Cutoff Current	Іево	V _{EB} =3V,I _C =0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} =5V,I _C =1mA	70		200	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	Ic=10mA,I _B =1mA			0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	Ic=10mA,I _B =1mA			1.4	V
Transition frequency	fT	V _{CE} =5V,I _C =5mA f=400MHz		800		MHz



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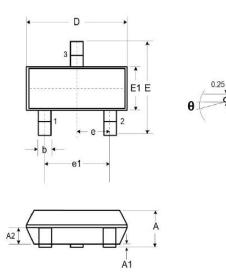
> Typical Performance Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)





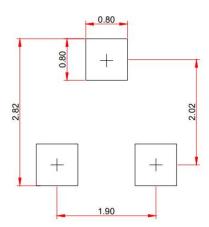


Package Information



DIM	Millimeters				
DIN	Min.	Тур.	Max.		
Α	0.89	-	1.12		
A1	0.01	-	0.10		
A2	0.88	0.95	1.02		
b	0.30	-	0.51		
С	0.08	-	0.18		
D	2.80	2.90	3.04		
E	2.10	2.37	2.64		
E1	1.20	1.30	1.40		
е	1.90				
e1	0.95				
L	0.40	0.50	0.60		
L1	0.55				
N	3				
θ	0°	-	8°		

Recommended Pad outline (Unit: mm)



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